



Ruttonsha International Rectifier Ltd.

SILICON CONTROLLED RECTIFIERS

High Power Thyristor Hockey Puk Version U-PUK Series 3000PU

Types : 3000PU 450 to 3000PU 520

FEATURES

- ❖ Center amplifying gate.
- ❖ Metal case with ceramic insulator
- ❖ High profile hockey - puk.

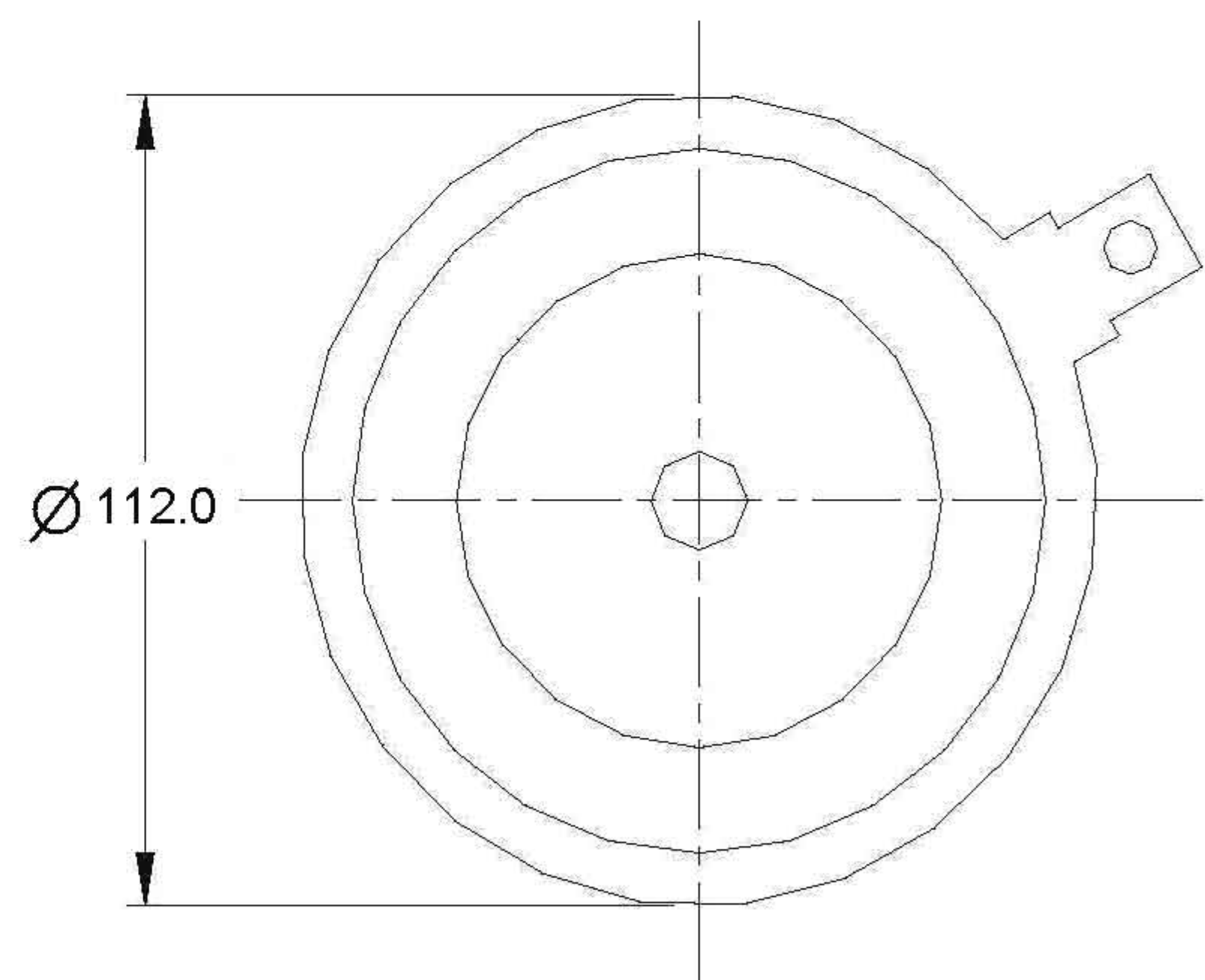
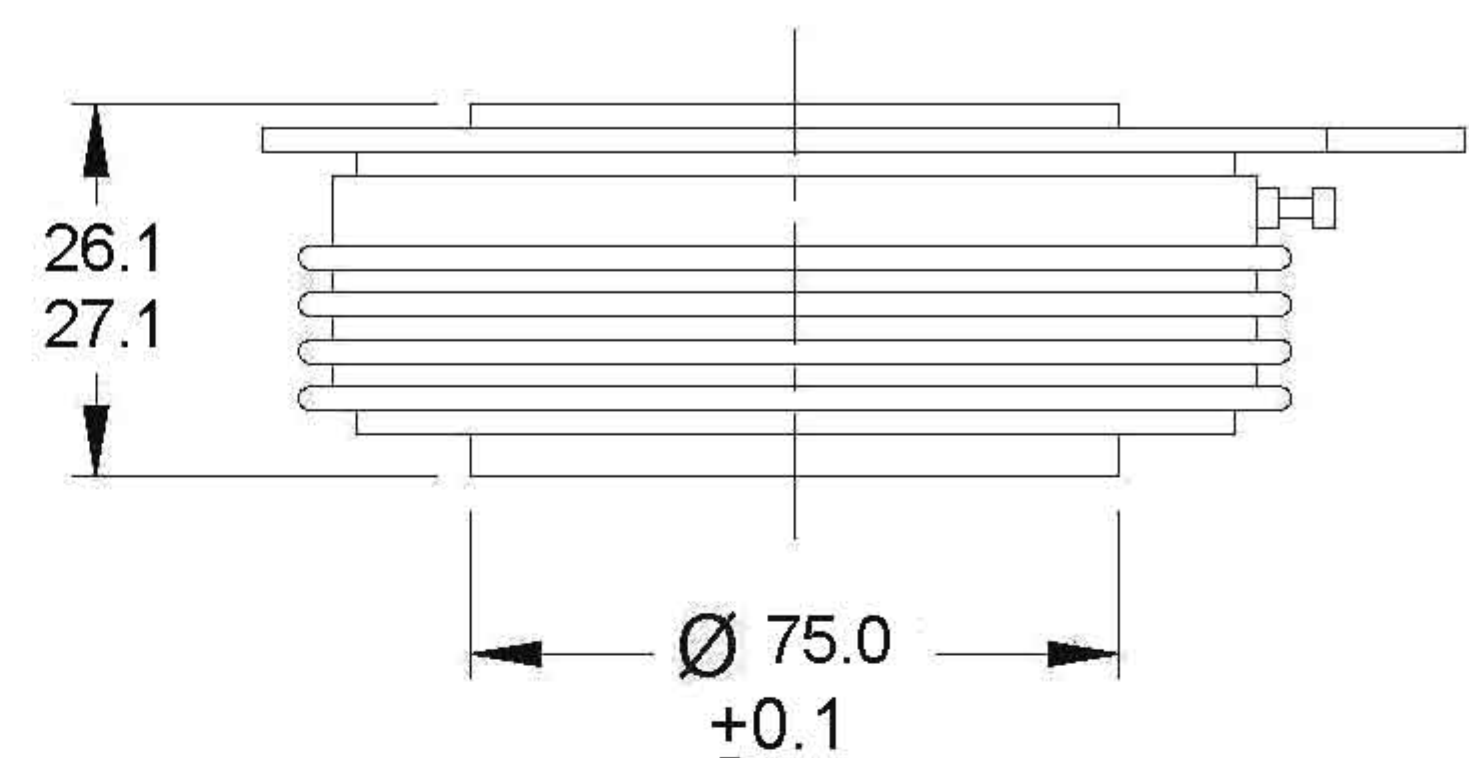
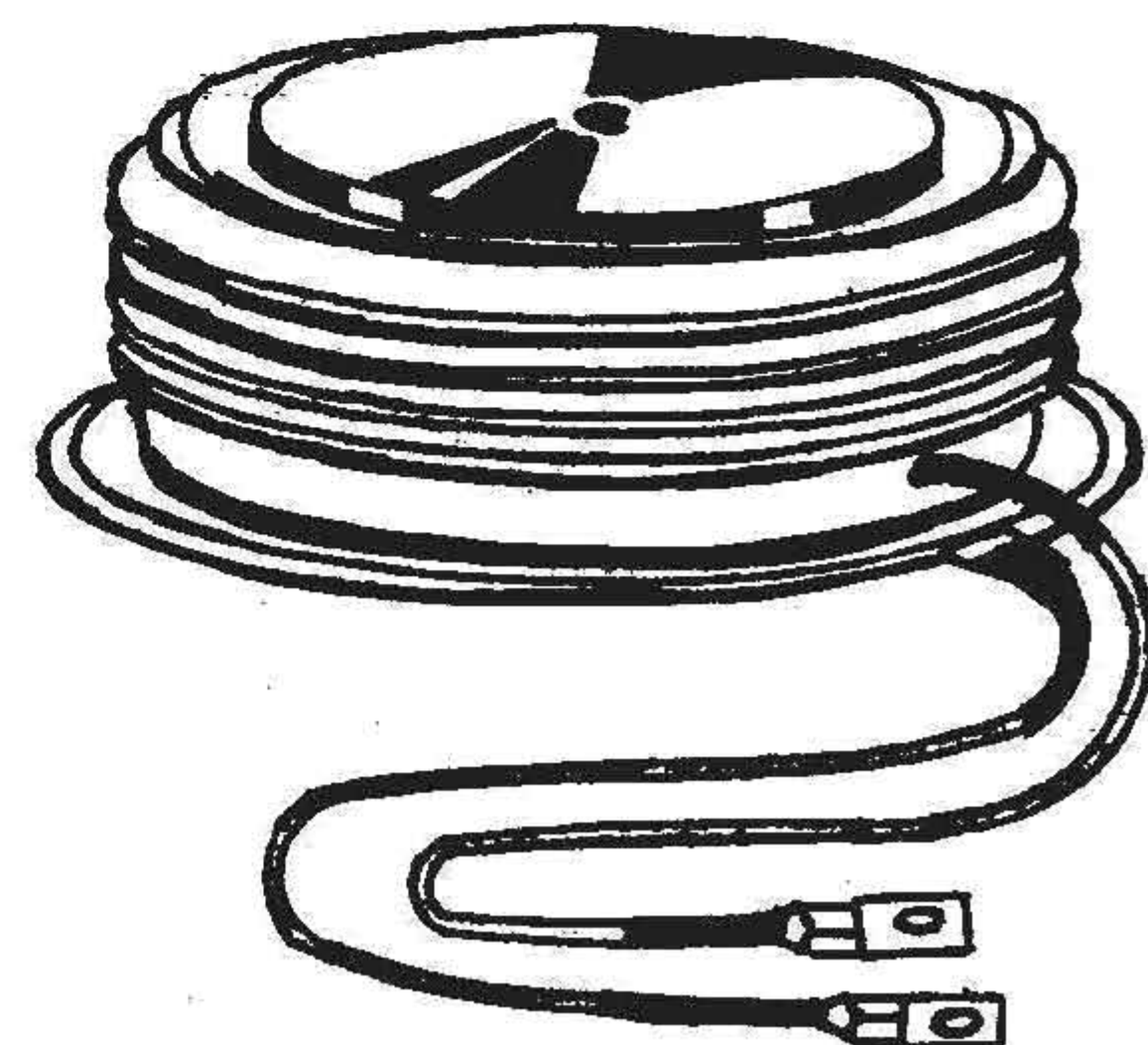
TYPICAL APPLICATIONS

- ❖ DC motor control (e.g. for machine tools).
- ❖ Controlled rectifiers (e.g. for battery charging, Uninterrupted Power Supply).
- ❖ AC controllers (e.g. for temperature control, lights control).

Major Ratings and Characteristics

Parameter	3000PU	Units
$I_{T(AV)}$	2960	A
@ T_{hs}	55	°C
$I_{T(RMS)}$	5825	A
@ T_{hs}	55	°C
I_{TSM}	@ 50 Hz	36 KA
I^2t	@ 50 Hz	6480 KA^2s
V_{DRM}/V_{RRM}	4500 to 5200	V
t_q	typical	800 μs
T_J	-40 to +125	°C

3000PU (U - PUK)



All dimension in millimeters

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ELECTRICAL SPECIFICATIONS

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Voltage Ratings

Type number	Voltage Code	V_{DRM}/V_{RRM} , max repetitive peak and off-state voltage V	V_{RSM} , maximum non-repetitive peak voltage V	I_{DRM}/I_{RRM} max. @ $T_J = T_J$ max. mA
3000PU	450	4500 / 4500	4600	150
	480	4800 / 4800	4900	
	500	5000 / 5000	5100	
	520	5200 / 5200	5300	

On - state Conduction

Parameter		3000PU	Units	Conditions		
I _{T(AV)}	Max. average on-state current	2960	A	180° conduction, half sine wave		
	@ Heatsink temperature	55	°C	double side cooled		
I _{T(RMS)}	Max RMS on-state current	5825	A	DC @55°C heatsink temperature double side cooled		
I _{TSM}	Max. peak, one-cycle non-repetitive surge current	36	KA	t = 10 ms	No voltage reappplied	Sinusoidal half wave, Initial T _J =T _J max.
I ² t	Maximum I ² t for fusing	6480	KA ² s	t = 10 ms		
V _{T(TO)}	Threshold voltage	1.3	V	T _J =T _J max.		
r _t	on-state slope resistance	0.24	mΩ	T _J =T _J max.		
V _{TM}	Max. on state voltage	2.1	V	I _{PK} = 4000 A,T _J =T _J max, t _P = 10 ms sine pulse		
I _H	Maximum holding current	1000	mA	T _J = 25°C , anode supply 12 V resistive load		

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Switching

Parameter	3000PU	Units	Conditions
di/dt Max. non-repetitive rate of rise of turned-on current	100	A/μs	Gate drive 20V, 20Ω, $t_r \leq 0.5\mu s$, $I_{FG} = 2A$ $T_J = T_J \text{ max. anode voltage} \leq 60\% V_{DRM}$
t_q Typical turn-off time	800	μs	$I_{TM} = 4000 A$, $T_J = T_J \text{ max.}$ di/dt = 10 A/μs, $V_R = 100V$ dv/dt = 20 V/μs, 0.8 V_{DRM} Reapplied, $t_p = 2ms$

Blocking

Parameter	3000PU	Units	Conditions
dv/dt Maximum critical rate of rise of off-state voltage	500	V/μs	$T_J = T_J \text{ max.}$
I_{RRM} I_{DRM} Max. peak reverse and off-state leakage current	150	mA	$T_J = T_J \text{ max. rated } V_{DRM} / V_{RRM} \text{ applied}$

Triggering

Parameter	3000PU	Units	Conditions
P_{GM} Maximum peak gate power	50	W	$T_J = T_J \text{ max.}, t_p \leq 5 \text{ ms}$
$P_{G(AV)}$ Maximum average gate power	5		$T_J = T_J \text{ max.}, f = 50Hz, d\% = 50$
I_{GM} Max. peak positive gate current	3.0	A	$T_J = T_J \text{ max.}, t_p \leq 5 \text{ ms}$
$+V_{GM}$ Maximum peak positive gate voltage	20	V	$T_J = T_J \text{ max.}, t_p \leq 5 \text{ ms}$
$-V_{GM}$ Maximum peak negative gate voltage	5.0		
I_{GT} DC gate current required to trigger	300	mA	$T_J = 25^\circ C$ Max.required gate trigger/ current/voltage are the lowest value which will trigger all units 12 V anode-to-cathode applied
V_{GT} DC gate voltage required to trigger	3.0	V	$T_J = 25^\circ C$
I_{GD} DC gate current not to trigger	10	mA	$T_J = T_J \text{ max.}$ Max. gate current/voltage not to trigger is the max. value which will not trigger any unit with rated V_{DRM} anode-to-cathode applied
V_{GD} DC gate voltage not to trigger	0.25	V	

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Thermal and Mechanical Specifications

Parameter		3000PU	Units	Conditions
T _J	Max.operating temperature range	-40 TO +125	°C	
T _{stg}	Max.storage temperature range	-40 TO +150		
R _{thJ-hs}	Max. thermal resistance, junction to heatsink	0.008	K/W	DC operation double side cooled
F	Mounting force, ± 10% ,	63 TO 77	KN	
wt.	Approximate weight	1200	g	
Case style		U - PUK		See Outline Table

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Curves

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Figure 1 - On-state characteristics of Limit device

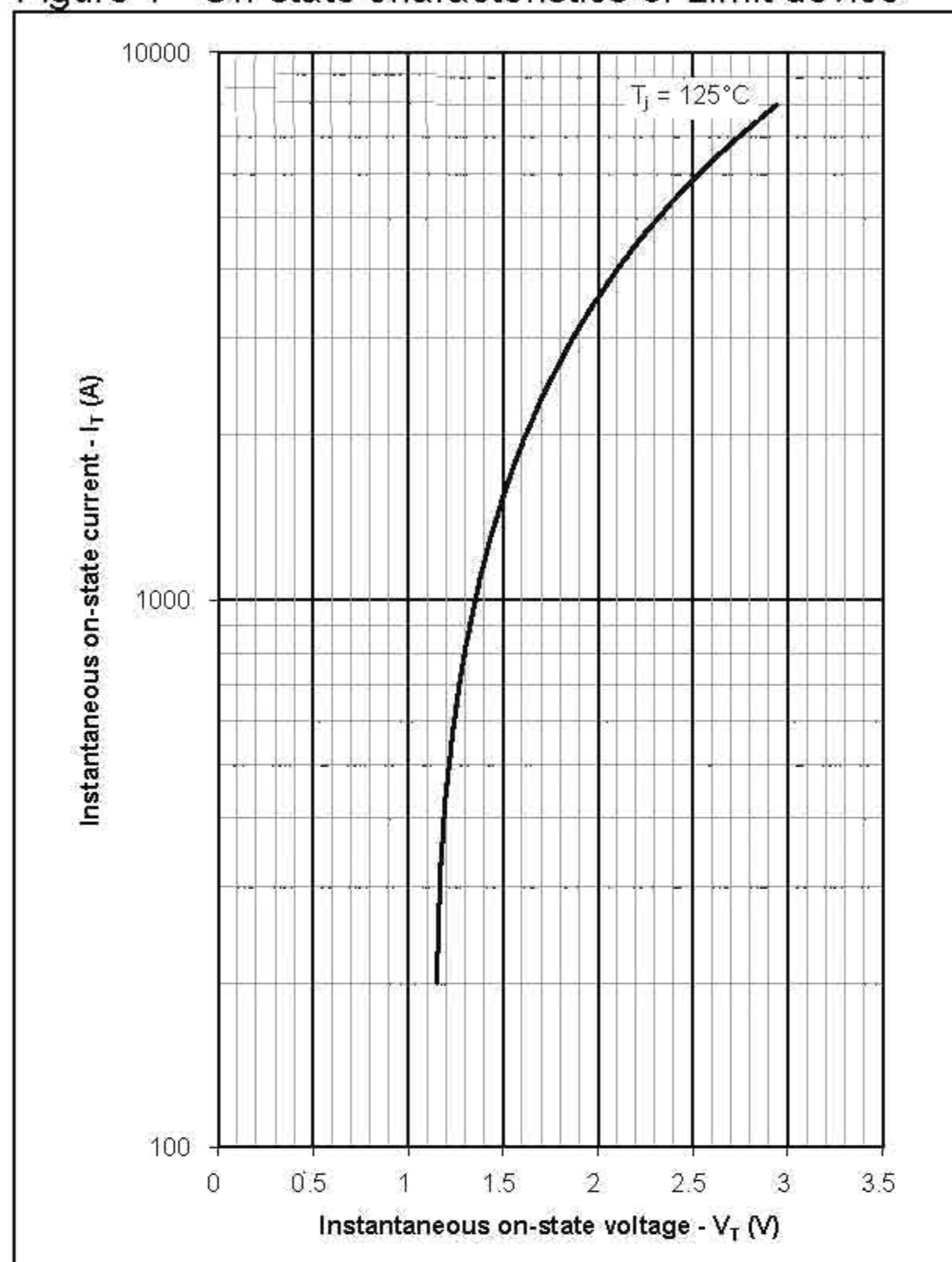


Figure 2 - Transient thermal impedance

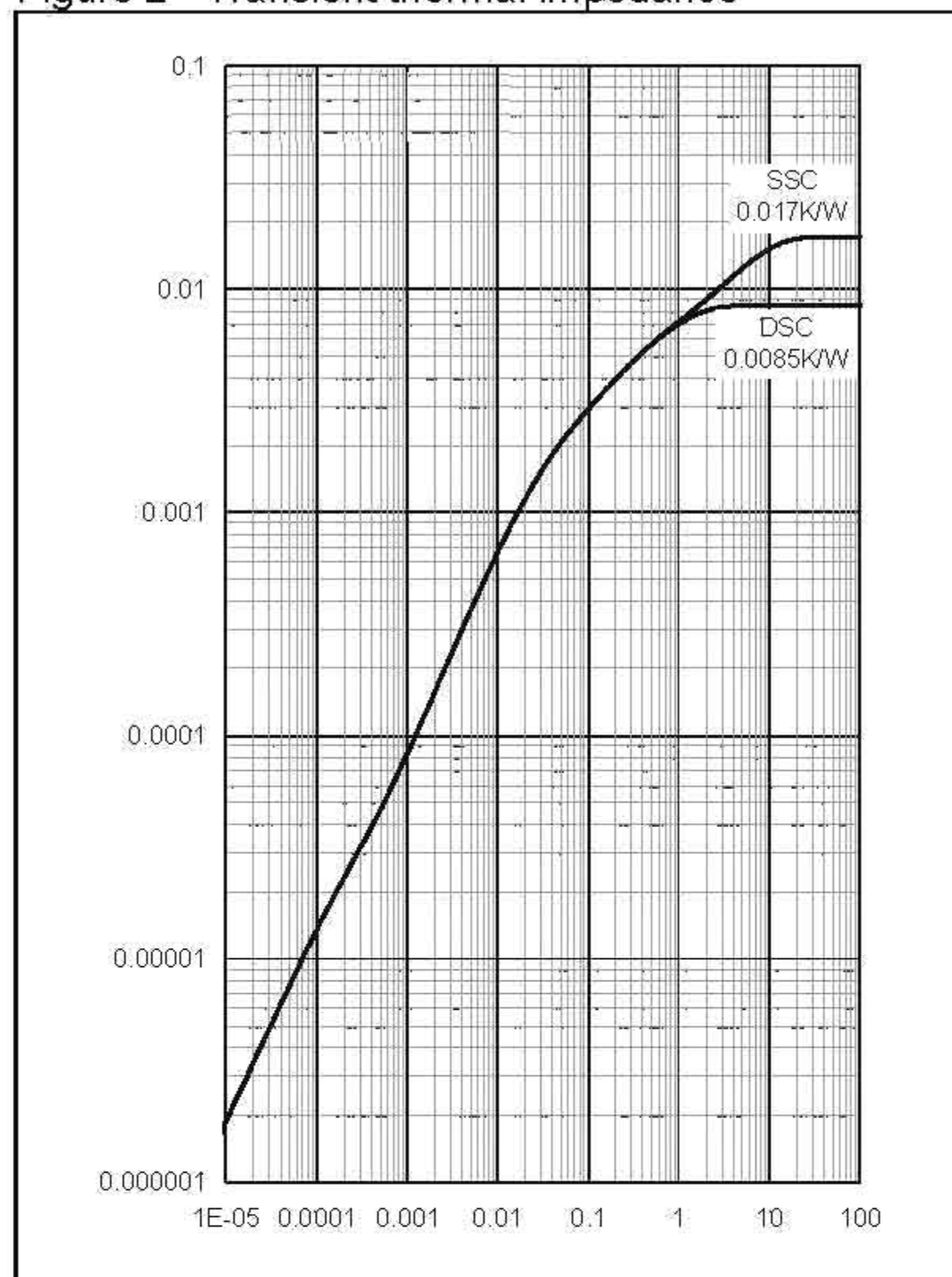


Figure 3 - On-state current vs. Power dissipation - Double Side Cooled (Sine wave)

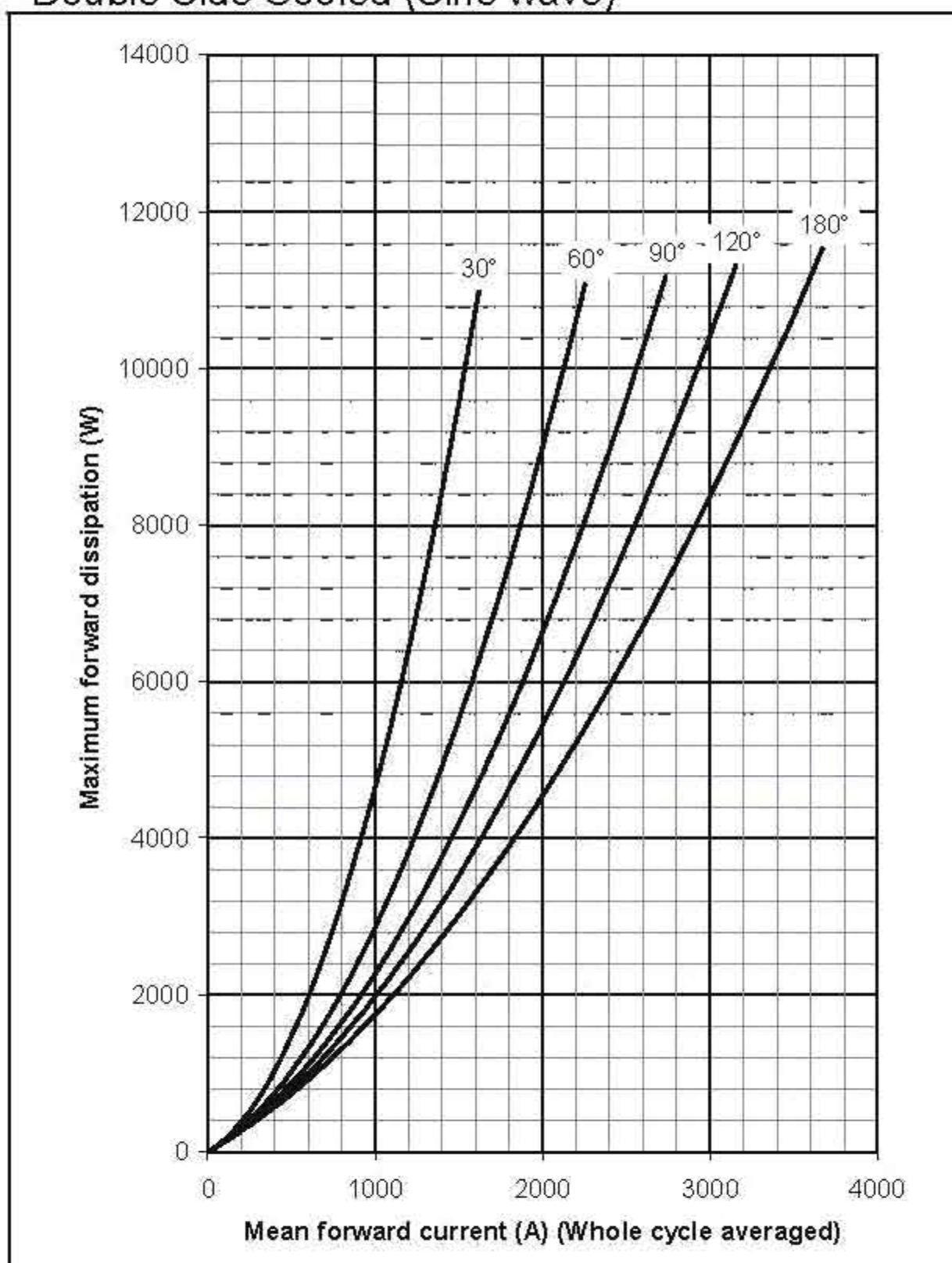
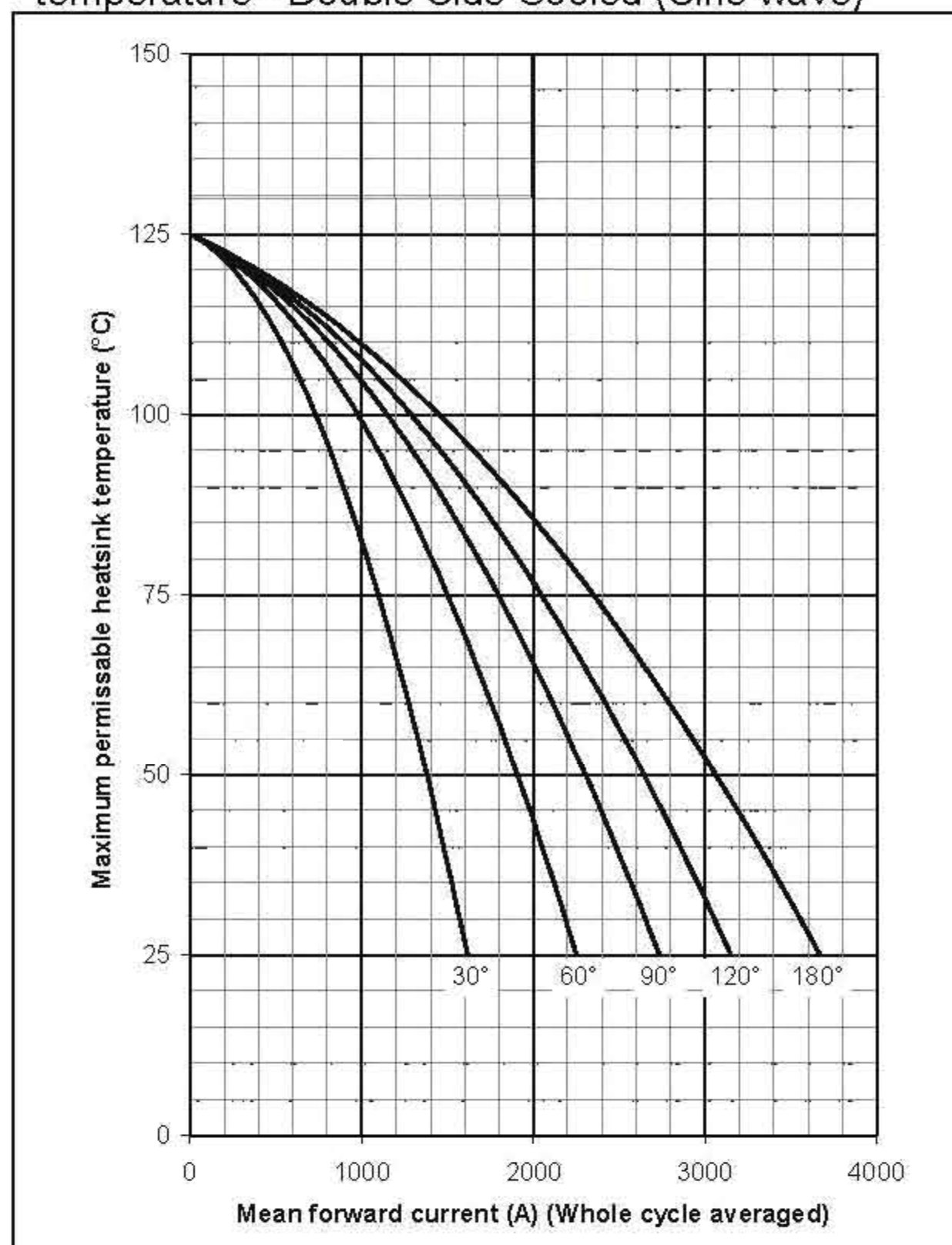


Figure 4 - On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)



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Figure 5 - Maximum surge and I^2t Ratings

